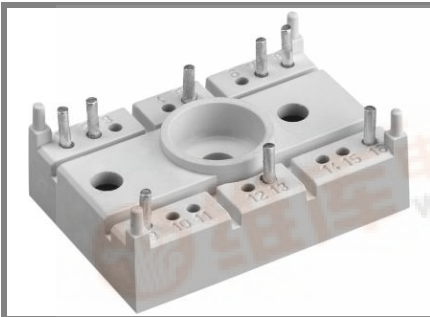


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SEMITOP® 2

Bridge Rectifier

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Target Data

Features

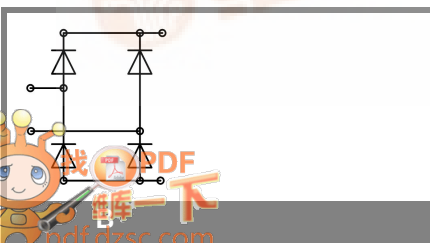
- Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast diodes
- UL recognized, file no. E 63 532

Typical Applications

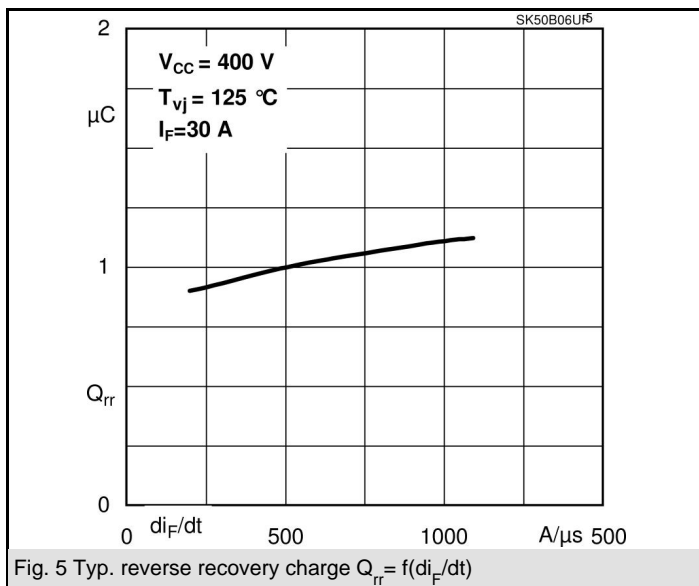
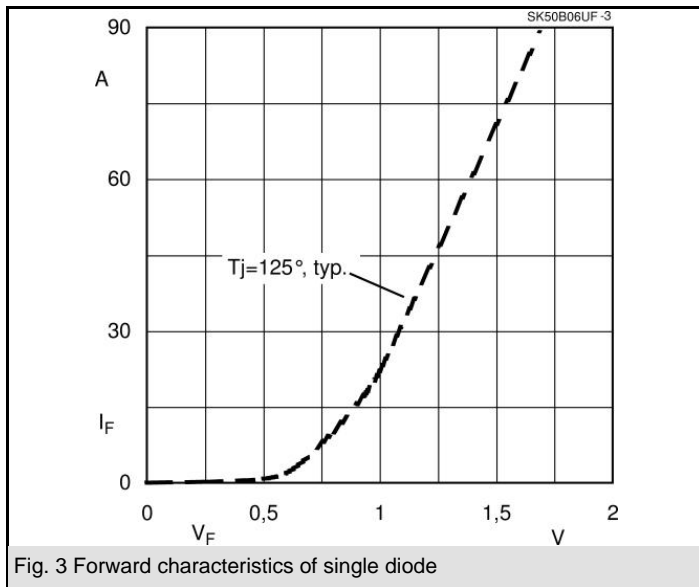
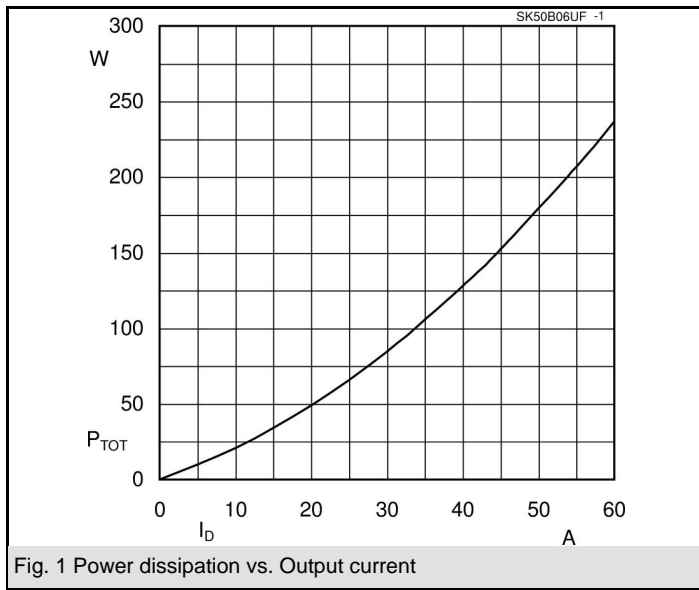
- General power switching applications
- UPS
- SMPS
- Welding equipment

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 46$ A (full conduction) ($T_s = 80$ °C)
600	600	SK 50 B 06 UF

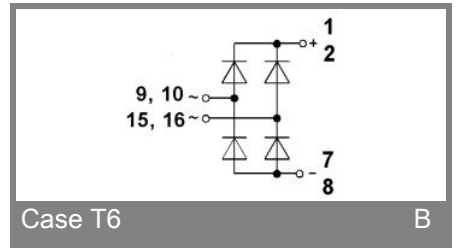
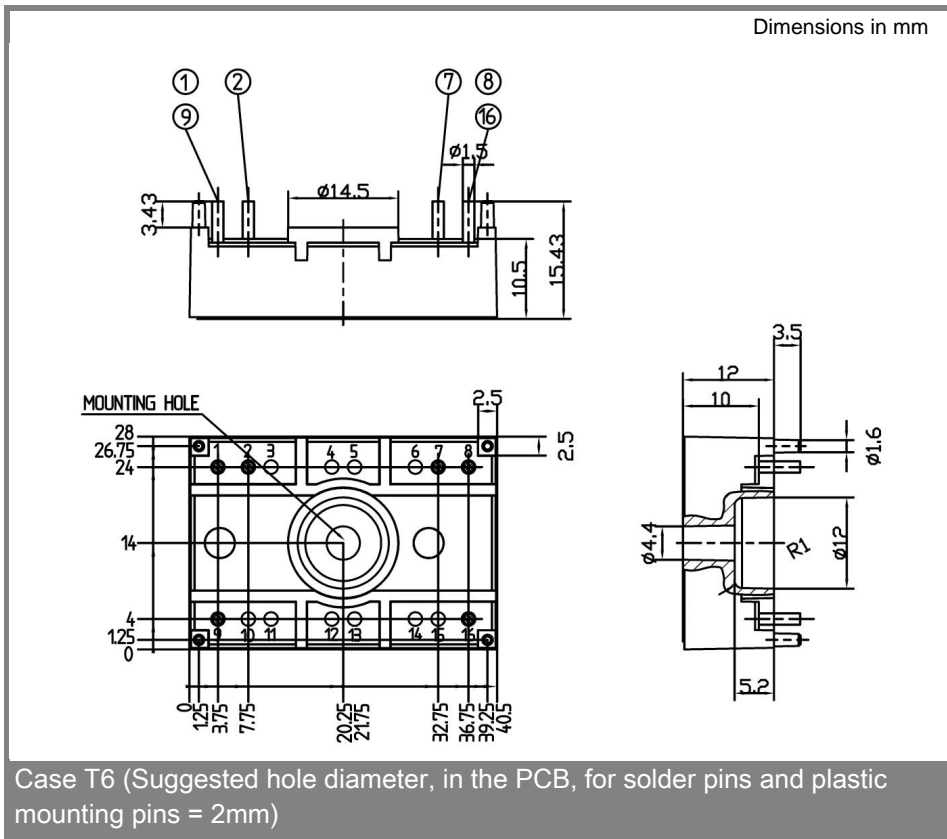
Symbol	Conditions	Values	Units
I_D	$T_s = 80$ °C	46	A
I_{RRM}	$T_{vj} = 125$ °C; $V_R = 400$ V; $I_F = 30$ A;	11	A
Q_{rr}	$-di_F/dt = 300$ A/μs	typ. 0,93	μC
I_R	$T_{vj} = 25$ (150) °C; $V_R = V_{RRM}$	max 0,015 (0,475)	mA
I_{FSM}	$T_{vj} = 150$ °C; 10 ms	400	A
i^2t	$T_{vj} =$ °C; ms	800	A
	$T_{vj} = 150$ °C; 10 ms		A²s
	$T_{vj} =$ °C; ms		A²s
V_F	$T_{vj} = 125$ °C; $I_F = 50$ A	max. 1,95	V
$V_{(TO)}$	$T_{vj} = 125$ °C	max. 0,8	V
r_T	$T_{vj} = 125$ °C	max. 11	mΩ
I_{RD}	$T_{vj} =$ °C; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$		mA
$R_{th(j-s)}$	per diode	1,8	K/W
	per module	0,45	K/W
T_{solder}	terminals, 10s	260	°C
T_{vj}		-40...+150	°C
T_{stg}		-40...+125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 (2500)	V
M_s	mounting torque to heatsink	2	Nm
M_t			
m	approx. weight	19	g
Case	SEMITOP® 2	T 6	



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